

Quad Channel, High Speed Digital Isolators

Data Sheet

ADuM3440/ADuM3441/ADuM3442

FEATURES

Low power operation

5 V operation

1.7 mA per channel maximum @ 0 Mbps to 2 Mbps 68 mA per channel maximum @ 150 Mbps

3.3 V operation

1.0 mA per channel maximum @ 0 Mbps to 2 Mbps

33 mA per channel maximum @ 150 Mbps

Bidirectional communication

3.3 V/5 V level translation

High temperature operation: 105°C High data rate: dc to 150 Mbps (NRZ)

Precise timing characteristics
5 ns maximum pulse width distortion

5 ns maximum channel-to-channel matching

High common-mode transient immunity: >25 kV/μs

Output enable function

16-lead SOIC wide body package

Safety and regulatory approvals

UL recognition: 2500 V rms for 1 minute per UL 1577

CSA Component Acceptance Notice #5A

VDE certificate of conformity

DIN V VDE V 0884-10 (VDE V 0884-10):2006-12

 $V_{IORM} = 560 V peak$

APPLICATIONS

High speed multichannel isolation SPI interface/data converter isolation Instrumentation

GENERAL DESCRIPTION

The ADuM344x¹ are four channel, digital isolators based on the Analog Devices, Inc., *i*Coupler® technology supporting data rates up to 150 Mbps. Combining high speed CMOS and monolithic air core transformer technology, these isolation components provide outstanding performance characteristics superior to alternatives such as optocoupler devices.

By avoiding the use of LEDs and photodiodes, *i*Coupler devices remove the design difficulties commonly associated with optocouplers. The typical optocoupler concerns regarding uncertain current transfer ratios, nonlinear transfer functions, and temperature and lifetime effects are eliminated with the simple *i*Coupler digital interfaces and stable performance characteristics. The need for external drivers and other discrete components is eliminated with these *i*Coupler products.

¹ Protected by U.S. Patents 5,952,849; 6,873,065; 6,903,578; and 7,075,329.

Rev. D

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FUNCTIONAL BLOCK DIAGRAMS

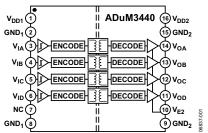


Figure 1. ADuM3440 Functional Block Diagram

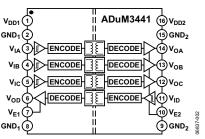


Figure 2. ADuM3441 Functional Block Diagram

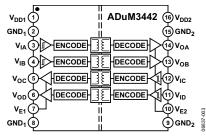


Figure 3. ADuM3442 Functional Block Diagram

Furthermore, *i*Coupler devices consume one-tenth to one-sixth the power of optocouplers at comparable signal data rates.

The ADuM344x isolators provide four independent isolation channels in a variety of channel configurations (see the Ordering Guide). The ADuM344x operates with the supply voltage on either side ranging from 3.0 V to 5.5 V, providing compatibility with lower voltage systems as well as enabling voltage translation functionality across the isolation barrier. In addition, the ADuM344x provides low pulse width distortion and tight channel-to-channel matching. Unlike other optocoupler alternatives, the ADuM344x isolators have a patented refresh feature that ensures dc correctness in the absence of input logic transitions and during the power-up/power-down condition.

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2/12—Rev. C to Rev. D	9/08—Rev. A to Rev. B
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	5/08—Rev. 0 to Rev. A

11/07—Rev. 0: Initial Version

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SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

All voltages are relative to their respective ground. 4.5 V \leq V $_{DD1} \leq$ 5.5 V, 4.5 V \leq V $_{DD2} \leq$ 5.5 V. All minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at $T_A = 25$ °C, $V_{DD1} = V_{DD2} = 5$ V.

Table 1.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	I _{DDI (Q)}		0.75	1.3	mA	
Output Supply Current per Channel, Quiescent	I _{DDO (Q)}		0.5	1.2	mA	
ADuM3440, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}		3	3.9	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		2	3	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}		120	220	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}		47	55	mA	75 MHz logic signal frequency
ADuM3441, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}		2.8	3.6	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		2.3	2.9	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}		101	165	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}		65	80	mA	75 MHz logic signal frequency
ADuM3442, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (Q)} , I _{DD2 (Q)}		2.5	3.5	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (150)} , I _{DD2 (150)}		83	130	mA	75 MHz logic signal frequency
For All Models						
Input Currents	I _{IA} , I _{IB} , I _{IC} ,	-10	+0.01	+10	μΑ	$0 \le V_{IA}$, V_{IB} , V_{IC} , $V_{ID} \le V_{DD1}$ or V_{DD2} ,
	I_{ID} , I_{E1} , I_{E2}					$0 \le V_{E1}$, $V_{E2} \le V_{DD1}$ or V_{DD2}
Logic High Input Threshold	V _{IH} , V _{EH}	2.0			V	
Logic Low Input Threshold	V _{IL} , V _{EL}			0.8	V	
Logic High Output Voltages	$V_{OAH}, V_{OBH}, V_{OCH}, V_{ODH}$	$(V_{DD1} \text{ or } V_{DD2}) - 0.1$	5.0		V	$I_{Ox} = -20 \mu A, V_{Ix} = V_{IxH}$
		$(V_{DD1} \text{ or } V_{DD2}) - 0.4$	4.8		V	$I_{Ox} = -4 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Voltages	$V_{OAL}, V_{OBL}, V_{OCL}, V_{ODL}$		0.0	0.1	V	$I_{Ox} = 20 \mu A, V_{Ix} = V_{IxL}$
			0.04	0.1	V	$I_{Ox} = 400 \ \mu A, V_{Ix} = V_{IxL}$
			0.2	0.4	V	$I_{Ox} = 4 \text{ mA}, V_{Ix} = V_{IxL}$
SWITCHING SPECIFICATIONS				,		
Minimum Pulse Width ²	PW			6.67	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Maximum Data Rate ³		150			Mbps	$C_L = 15 \text{ pF, CMOS signal levels}$
Propagation Delay ⁴	t _{PHL} , t _{PLH}	20		32	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^5$	PWD		0.5	2	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Change vs. Temperature			3		ps/°C	$C_L = 15 \text{ pF, CMOS signal levels}$
Propagation Delay Skew ⁶	t _{PSK}			12	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Channel-to-Channel Matching, Codirectional Channels⁵	t _{PSKCD}			2	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Channel-to-Channel Matching, Opposing Directional Channels⁵	t _{PSKOD}			5	ns	C _L = 15 pF, CMOS signal levels

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
For All Models			,			
Output Disable Propagation Delay (High/Low to High Impedance)	t _{PHZ} , t _{PLH}		6	8	ns	C _L = 15 pF, CMOS signal levels
Output Enable Propagation Delay (High Impedance to High/Low)	$t_{PZH'}$, t_{PZL}		6	8	ns	C _L = 15 pF, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t _R /t _F		2.5		ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Common-Mode Transient Immunity at Logic High Output ⁷	CM _H	25	35		kV/μs	$V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000 \text{ V}$, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁷	CM _L	25	35		kV/μs	$V_{lx} = 0 \text{ V}, V_{CM} = 1000 \text{ V},$ transient magnitude = 800 V
Refresh Rate	f _r		1.2		Mbps	
Input Dynamic Supply Current per Channel ⁸	I _{DDI (D)}		0.196		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	I _{DDO (D)}		0.1		mA/Mbps	

¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate may be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3440/ADuM3441/ADuM3442 channel configurations.

² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

 $^{^4}$ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{Ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{Ix} signal to the 50% level of the rising edge of the V_{Ox} signal.

⁵ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing-directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁶ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

 $^{^{7}}$ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_{o} > 0.8 \, V_{DDO}$. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_{o} < 0.8 \, V$. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—3.3 V OPERATION

All voltages are relative to their respective ground. $3.0~V \le V_{DD1} \le 3.6~V, 3.0~V \le V_{DD2} \le 3.6~V$. All minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at $T_A = 25^{\circ}C$, $V_{DD1} = V_{DD2} = 3.3~V$.

Table 2.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	I _{DDI (Q)}		0.43	0.90	mA	
Output Supply Current per Channel, Quiescent	I _{DDO (Q)}		0.3	0.60	mA	
ADuM3440, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}		1.7	2.4	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		1.2	1.7	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}		63	110	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}		17	25	mA	75 MHz logic signal frequency
ADuM3441, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}		1.6	2.2	mA	DC to 1 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (Q)}		1.3	1.9	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}		52	80	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}		29	40	mA	75 MHz logic signal frequency
ADuM3442, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (Q)} , I _{DD2 (Q)}		1.5	2.0	mA	DC to 1 MHz logic signal frequency
150 Mbps						
V _{DD1} or V _{DD2} Supply Current	I _{DD1 (150)} , I _{DD2 (150)}		40	66	mA	75 MHz logic signal frequency
For All Models						
Input Currents	I _{IA} , I _{IB} , I _{IC} ,	-10	+0.01	+10	μΑ	$0 \le V_{IA}$, V_{IB} , V_{IC} , $V_{ID} \le V_{DD1}$ or V_{DD2} ,
	I _{ID} , I _{E1} , I _{E2}					$0 \le V_{E1}$, $V_{E2} \le V_{DD1}$ or V_{DD2}
Logic High Input Threshold	V _{IH} , V _{EH}	1.6			V	
Logic Low Input Threshold	V _{IL} , V _{EL}			0.4	V	
Logic High Output Voltages	$V_{OAH}, V_{OBH}, V_{OCH}, V_{ODH}$	$(V_{DD1} \text{ or } V_{DD2}) - 0.1$	3.0		V	$I_{Ox} = -20 \mu A, V_{Ix} = V_{IxH}$
		(V _{DD1} or	2.8		V	$I_{Ox} = -4 \text{ mA, } V_{Ix} = V_{IxH}$
		V_{DD2}) – 0.4				
Logic Low Output Voltages	V _{OAL} , V _{OBL} , V _{OCL} , V _{ODL}		0.0	0.1	V	$I_{Ox} = 20 \mu A, V_{Ix} = V_{IxL}$
	V OCL, V ODL		0.04	0.1	V	$I_{Ox} = 400 \mu A, V_{Ix} = V_{IxL}$
			0.2	0.4	V	$I_{Ox} = 4 \text{ mA, } V_{Ix} = V_{IxL}$
WITCHING SPECIFICATIONS					†	-Ox ····· y · IX · IXL
Minimum Pulse Width ²	PW			6.67	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Maximum Data Rate ³		150			Mbps	$C_L = 15 \text{ pF}$, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	20		36	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^4$	PWD		0.5	2	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Change vs. Temperature			3	_	ps/°C	$C_L = 15 \text{ pF, CMOS signal levels}$
Propagation Delay Skew ⁵	t _{PSK}		-	16	ns	$C_L = 15 \text{ pF}$, CMOS signal levels
Channel-to-Channel Matching,	t _{PSKCD}			2	ns	$C_1 = 15 \text{ pF}$, CMOS signal levels
Codirectional Channels ⁶	-PSKCD			-		
Channel-to-Channel Matching,	t _{PSKOD}			5	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Opposing Directional Channels ⁵						

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
For All Models						
Output Disable Propagation Delay (High/Low to High Impedance)	t _{PHZ} , t _{PLH}		6	8	ns	C _L = 15 pF, CMOS signal levels
Output Enable Propagation Delay (High Impedance to High/Low)	t _{PZH} , t _{PZL}		6	8	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Output Rise/Fall Time (10% to 90%)	t _R /t _F		3		ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Common-Mode Transient Immunity at Logic High Output ⁷	CM _H	25	35		kV/μs	$V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000 \text{ V}$, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁷	CM _L	25	35		kV/μs	$V_{lx} = 0 \text{ V}, V_{CM} = 1000 \text{ V},$ transient magnitude = 800 V
Refresh Rate	f _r		1.1		Mbps	
Input Dynamic Supply Current per Channel ⁸	I _{DDI (D)}		0.076		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	I _{DDO (D)}		0.028		mA/Mbps	

¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate may be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3440/ADuM3441/ADuM3442 channel configurations.

² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

 $^{^4}$ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{Ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{Ix} signal to the 50% level of the V_{Ox} signal.

⁵ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁶ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

 $^{^7}$ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining V_o > 0.8 V_{DDO}. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining V_o < 0.8 V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—MIXED 5 V/3.3 V OR 3.3 V/5 V OPERATION

All voltages are relative to their respective ground. 5 V/3.3 V operation: $4.5 \text{ V} \le V_{DD1} \le 5.5 \text{ V}$, $3.0 \text{ V} \le V_{DD2} \le 3.6 \text{ V}$; 3 V/5 V operation: $3.0 \text{ V} \le V_{DD1} \le 3.6 \text{ V}$, $4.5 \text{ V} \le V_{DD2} \le 5.5 \text{ V}$. All minimum/maximum specifications apply over the entire recommended operating range, unless otherwise noted. All typical specifications are at $T_A = 25^{\circ}\text{C}$; $V_{DD1} = 3.3 \text{ V}$, $V_{DD2} = 5 \text{ V}$ or $V_{DD1} = 5 \text{ V}$, $V_{DD2} = 3.3 \text{ V}$.

Table 3.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS			,			
Input Supply Current per Channel, Quiescent	I _{DDI (Q)}					
5 V/3.3 V Operation			0.75	1.3	mA	
3.3 V/5 V Operation			0.43	0.9	mA	
Output Supply Current per Channel, Quiescent	I _{DDO (Q)}					
5 V/3.3 V Operation			0.3	0.7	mA	
3.3 V/5 V Operation			0.5	1.2	mA	
ADuM3440, Total Supply Current, Four Channels 1						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}					
5 V/3.3 V Operation			3	3.9	mA	DC to 1 MHz logic signal frequenc
3.3 V/5 V Operation			1.7	2.4	mA	DC to 1 MHz logic signal frequence
V _{DD2} Supply Current	I _{DD2 (Q)}					
5 V/3.3 V Operation	332(4)		1.2	1.7	mA	DC to 1 MHz logic signal frequence
3.3 V/5 V Operation			2	3	mA	DC to 1 MHz logic signal frequence
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}					
5 V/3.3 V Operation	221(130)		120	220	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			63	110	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}					
5 V/3.3 V Operation	(,		17	25	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			47	55	mA	75 MHz logic signal frequency
ADuM3441, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}					
5 V/3.3 V Operation	351(4)		2.8	3.6	mA	DC to 1 MHz logic signal frequence
3.3 V/5 V Operation			1.6	2.2	mA	DC to 1 MHz logic signal frequence
V _{DD2} Supply Current	I _{DD2 (Q)}					
5 V/3.3 V Operation			1.3	1.9	mA	DC to 1 MHz logic signal frequence
3.3 V/5 V Operation			2.3	2.9	mA	DC to 1 MHz logic signal frequence
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}					
5 V/3.3 V Operation	221(130)		101	165	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			52	80	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}					
5 V/3.3 V Operation			29	40	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			65	80	mA	75 MHz logic signal frequency
ADuM3442, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1 (Q)}					
5 V/3.3 V Operation	55.(9)		2.5	3.5	mA	DC to 1 MHz logic signal frequence
3.3 V/5 V Operation			1.5	2.0	mA	DC to 1 MHz logic signal frequence
V _{DD2} Supply Current	I _{DD2 (Q)}					3 2 3 2 3 4
5 V/3.3 V Operation	552 (Q)		1.5	2.0	mA	DC to 1 MHz logic signal frequenc
3.3 V/5 V Operation			2.5	3.5	mA	DC to 1 MHz logic signal frequence

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
150 Mbps						
V _{DD1} Supply Current	I _{DD1 (150)}					
5 V/3.3 V Operation			83	130	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			40	66	mA	75 MHz logic signal frequency
V _{DD2} Supply Current	I _{DD2 (150)}					
5 V/3.3 V Operation	DD2 (130)		40	66	mA	75 MHz logic signal frequency
3.3 V/5 V Operation			83	130	mA	75 MHz logic signal frequency
For All Models			03	130	'''' '	, 5 m iz logic signal frequency
Input Currents	 I _{IA} , I _{IB} , I _{IC} ,	-10	+0.01	+10	μΑ	$0 \le V_{IA}, V_{IB}, V_{IC}, V_{ID} \le V_{DD1} \text{ or } V_{DD2},$
input currents	'IA' 'IB' 'IC' I _{ID} , I _{E1} , I _{E2}	-10	+0.01	+10	μΑ	$0 \le V_{IA}, V_{IB}, V_{IC}, V_{ID} \le V_{DD1}$ or V_{DD2} , $0 \le V_{F1}, V_{F2} \le V_{DD1}$ or V_{DD2}
Logic High Input Threshold	V _{IH} , V _{EH}					O = VE1, VE2 = VDD1 O1 VDD2
5 V/3.3 V Operation	V _{IH} , V _{EH}	2.0			V	
•		1.6			V	
3.3 V/5 V Operation	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	1.0			V	
Logic Low Input Threshold	V _{IL} , V _{EL}				.,	
5 V/3.3 V Operation				0.8	V	
3.3 V/5 V Operation			0.4	0.4	V	
Logic High Output Voltages	V _{OAH} , V _{OBH} ,	(V _{DD1} or	(V _{DD1} or		V	$I_{Ox} = -20 \mu A, V_{Ix} = V_{IxH}$
	V_{OCH} , V_{ODH}	V_{DD2}) – 0.1	V _{DD2})			
		(V _{DD1} or	$(V_{DD1} \text{ or } Q)$		V	$I_{Ox} = -4 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Valtages	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	V_{DD2}) – 0.4	V_{DD2}) - 0.2	0.1	\ \ \	1 - 20 4 . 1/
Logic Low Output Voltages	$V_{OAL}, V_{OBL}, V_{OCL}, V_{ODL}$		0.0	0.1	V	$I_{Ox} = 20 \mu A, V_{Ix} = V_{IxL}$
	V _{OCL} , V _{ODL}		0.04	0.1	V	$I_{0x} = 400 \mu A, V_{1x} = V_{1x1}$
				0.1 0.4	V	OX I IX IXE
CWITCHING CRECIFICATIONS			0.2	0.4	V	$I_{Ox} = 4 \text{ mA}, V_{Ix} = V_{IxL}$
SWITCHING SPECIFICATIONS	514					
Minimum Pulse Width ²	PW			6.67	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Maximum Data Rate ³		150			Mbps	$C_L = 15 \text{ pF, CMOS signal levels}$
Propagation Delay ⁴	t _{PHL} , t _{PLH}	20		35	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^4$	PWD		0.5	2	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Change vs. Temperature			3		ps/°C	$C_L = 15 \text{ pF, CMOS signal levels}$
Propagation Delay Skew⁵	t _{PSK}			15	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Channel-to-Channel Matching,	t _{PSKCD}			2	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Codirectional Channels ⁶						
Channel-to-Channel Matching,	t _{PSKOD}			5	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
Opposing Directional Channels⁵						
For All Models						
Output Disable Propagation Delay	t _{PHZ} , t _{PLH}		6	8	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
(High/Low to High Impedance)						
Output Enable Propagation Delay	t _{PZH} , t _{PZL}		6	8	ns	$C_L = 15 \text{ pF, CMOS signal levels}$
(High Impedance to High/Low)						
Output Rise/Fall Time (10% to 90%)	t _R /t _F					$C_L = 15 \text{ pF, CMOS signal levels}$
5 V/3 V Operation			3.0		ns	
3 V/5 V Operation			2.5		ns	
Common-Mode Transient Immunity	CM _H	25	35		kV/μs	$V_{lx} = V_{DD1}$ or V_{DD2} , $V_{CM} = 1000 \text{ V}$,
at Logic High Output ⁷	lent !	25	25		1377	transient magnitude = 800 V
Common-Mode Transient Immunity	CM _L	25	35		kV/μs	$V_{lx} = 0 \text{ V}, V_{CM} = 1000 \text{ V},$ transient magnitude = 800 V
at Logic Low Output ⁷						transiem magnitude = 800 V
Refresh Rate	f _r		4.3			
5 V/3.3 V Operation			1.2		Mbps	
3.3 V/5 V Operation			1.1		Mbps	
Input Dynamic Supply Current per Channel ⁸	I _{DDI (D)}					
5 V/3.3 V Operation			0.196		mA/Mbps	
3.3 V/5 V Operation			0.076		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	I _{DDO (D)}					
5 V/3.3 V Operation			0.028		mA/Mbps	
3.3 V/5 V Operation			0.01		mA/Mbps	

ADuM3440/ADuM3441/ADuM3442

- ¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate may be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3440/ADuM3441 channel configurations.
- ² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is quaranteed.
- ³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.
- 4 t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{Ix} signal to the 50% level of the falling edge of the V_{Ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{Ix} signal to the 50% level of the rising edge of the V_{Ox} signal.
- ⁵ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.
- ⁶ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.
- 7 CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining V_o > 0.8 V_{DDO}. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining V_o < 0.8 V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.
- ⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

PACKAGE CHARACTERISTICS

Table 4.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Resistance (Input to Output) ¹	R _{I-O}		10 ¹²		Ω	
Capacitance (Input to Output) ¹	C _{I-O}		2.2		рF	f = 1 MHz
Input Capacitance ²	Cı		4.0		рF	
IC Junction-to-Case Thermal Resistance, Side 1	θ_{JCI}		33		°C/W	Thermocouple located at
IC Junction-to-Case Thermal Resistance, Side 2	θ_{JCO}		28		°C/W	center of package underside

¹ The device is considered a 2-terminal device; Pin 1 through Pin 8 are shorted together and Pin 9 through Pin 16 are shorted together.

REGULATORY INFORMATION

The ADuM344x is approved by the organizations listed in Table 5. Refer to Table 10 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

Table 5.

UL	CSA	VDE
Recognized under 1577 component recognition program ¹	Approved under CSA Component Acceptance Notice #5A	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 ²
Single protection, 2500 V rms isolation voltage	Basic insulation per CSA 60950-1-03 and IEC 60950-1, 800 V rms (1131 V peak) maximum working voltage	Reinforced insulation, 560 V peak
	Reinforced insulation per CSA 60950-1-03 and IEC 60950-1, 400 V rms (566 V peak) maximum working voltage	
File E214100	File 205078	File 2471900-4880-0001

¹ In accordance with UL 1577, each ADuM344x is proof tested by applying an insulation test voltage ≥3000 V rms for 1 sec (current leakage detection limit = 5 µA).

INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 6.

Parameter	Symbol	Value	Unit	Conditions
Rated Dielectric Insulation Voltage		2500	V rms	1-minute duration
Minimum External Air Gap (Clearance)	L(I01)	7.7 min	mm	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L(I02)	8.1 min	mm	Measured from input terminals to output terminals, shortest distance path along body
Minimum Internal Gap (Internal Clearance)		0.017 min	mm	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>175	٧	DIN IEC 112/VDE 0303 Part 1
Isolation Group		Illa		Material Group (DIN VDE 0110, 1/89, Table 1)

² Input capacitance is from any input data pin to ground.

² In accordance with DIN V VDE V 0884-10, each ADuM344x is proof tested by applying an insulation test voltage ≥1050 V peak for 1 sec (partial discharge detection limit = 5 pC). An asterisk (*) marking branded on the component designates DIN V VDE V 0884-10 approval.

DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS

These isolators are suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by protective circuits. The asterisk (*) marking on packages denotes DIN V VDE V 0884-10 approval.

Table 7.

Description	Conditions	Symbol	Characteristic	Unit
	Conditions	Syllibol	Characteristic	Onit
Installation Classification per DIN VDE 0110				
For Rated Mains Voltage ≤ 150 V rms			I to IV	
For Rated Mains Voltage ≤ 300 V rms			I to III	
For Rated Mains Voltage ≤ 400 V rms			I to II	
Climatic Classification			40/105/21	
Pollution Degree per DIN VDE 0110, Table 1			2	
Maximum Working Insulation Voltage		V _{IORM}	560	V peak
Input-to-Output Test Voltage, Method B1	$V_{IORM} \times 1.875 = V_{PR}$, 100% production test, $t_m = 1$ sec, partial discharge < 5 pC	V _{PR}	1050	V peak
Input-to-Output Test Voltage, Method A	$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC	V _{PR}		
After Environmental Tests Subgroup 1			896	V peak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{IORM} \times 1.2 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC		672	V peak
Highest Allowable Overvoltage	Transient overvoltage, $t_{TR} = 10$ seconds	V _{TR}	4000	V peak
Safety-Limiting Values	Maximum value allowed in the event of a failure (see Figure 4)			
Case Temperature		T _s	150	°C
Side 1 Current		I _{S1}	265	mA
Side 2 Current		I _{S2}	335	mA
Insulation Resistance at T _s	$V_{10} = 500 \text{ V}$	R _s	>109	Ω

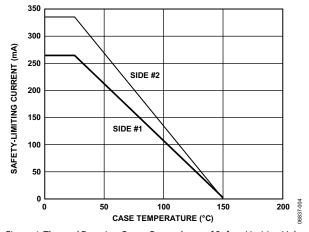


Figure 4. Thermal Derating Curve, Dependence of Safety-Limiting Values with Case Temperature per DIN V VDE V 0884-10

RECOMMENDED OPERATING CONDITIONS

Table 8.

Parameter	Rating
Operating Temperature Range, T _A	-40°C to +105°C
Supply Voltage Range, V _{DD1} , V _{DD2} 1	3.0 V to 5.5 V
Input Signal Rise and Fall Time	1.0 ms

¹ All voltages are relative to their respective ground. See the DC Correctness and Magnetic Field Immunity section for information on immunity to external magnetic fields.

ABSOLUTE MAXIMUM RATINGS

Ambient temperature = 25°C, unless otherwise noted.

Table 9.

Parameter	Rating		
Storage Temperature Range (T _{ST})	−65°C to +150°C		
Ambient Operating Temperature Range (T _A)	-40°C to +105°C		
Supply Voltages (V _{DD1} , V _{DD2}) ¹	−0.5 V to +7.0 V		
Input Voltage $(V_{IA}, V_{IB}, V_{IC}, V_{ID}, V_{E1}, V_{E2})^{1, 2}$	$-0.5 \mathrm{V} \mathrm{to} \mathrm{V}_{\mathrm{DD1}} + 0.5 \mathrm{V}$		
Output Voltage $(V_{OA}, V_{OB}, V_{OC}, V_{OD})^{1,2}$	$-0.5 \mathrm{V}$ to $\mathrm{V}_{\mathrm{DDO}} + 0.5 \mathrm{V}$		
Average Output Current per Pin ³			
Side 1 (I ₀₁)	–18 mA to +18 mA		
Side 2 (I _{O2})	-22 mA to +22 mA		
Common-Mode Transients (CM _H , CM _L) ⁴	−100 kV/µs to		
	+100 kV/μs		

¹ All voltages are relative to their respective ground.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 10. Maximum Continuous Working Voltage¹

Parameter	Max	Unit	Constraint
AC Voltage, Bipolar Waveform	565	V peak	50-year minimum lifetime
AC Voltage, Unipolar Waveform			
Basic Insulation	1131	V peak	Maximum approved working voltage per IEC 60950-1
Reinforced Insulation	560	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10
DC Voltage			
Basic Insulation	1131	V peak	Maximum approved working voltage per IEC 60950-1
Reinforced Insulation	560	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

Table 11. Truth Table (Positive Logic)

V _{IX} Input ¹	V _{EX} Input ²	V _{DDI} State ¹	V _{DDO} State ¹	V _{ox} Output ¹	Notes
Н	H or NC	Powered	Powered	Н	
L	H or NC	Powered	Powered	L	
Χ	L	Powered	Powered	Z	
Χ	H or NC	Unpowered	Powered	Н	Outputs return to the input state within 1 μ s of V_{DDI} power restoration.
X	L	Unpowered	Powered	Z	
X	X	Powered	Unpowered	Indeterminate	Outputs return to the input state within 1 μ s of V_{DDO} power restoration if V_{EX} state is H or NC. Outputs return to high impedance state within 8 ns of V_{DDO} power restoration if V_{EX} state is L.

¹ V_{IX} and V_{OX} refer to the input and output signals of a given channel (A, B, C, or D). V_{EX} refers to the output enable signal on the same side as the V_{OX} outputs. V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of the given channel, respectively.

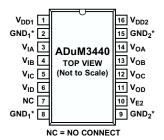
 $^{^2}$ V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of a given channel, respectively. See the PC Board Layout section.

³ See Figure 4 for maximum rated current values for various temperatures.

⁴ Refers to common-mode transients across the insulation barrier. Common-mode transients exceeding the Absolute Maximum Ratings can cause latch-up or permanent damage.

² In noisy environments, connecting V_{EX} to an external logic high or low is recommended.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

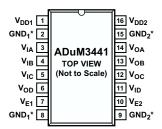


*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND_1 IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND_2 IS RECOMMENDED.

Figure 5. ADuM3440 Pin Configuration

Table 12. ADuM3440 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2, 8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
3	V _{IA}	Logic Input A.
4	V _{IB}	Logic Input B.
5	V _{IC}	Logic Input C.
6	V _{ID}	Logic Input D.
7	NC	No Connect.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V_{OA} , V_{OB} , V_{OC} , and V_{OD} outputs are enabled when V_{E2} is high or disconnected. V_{OA} , V_{OB} , V_{OC} , and V_{OD} outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.
11	V _{od}	Logic Output D.
12	V _{oc}	Logic Output C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
16	V_{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.

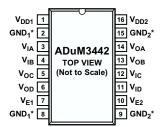


*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO ${\rm GND_1}$ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO ${\rm GND_2}$ IS RECOMMENDED.

Figure 6. ADuM3441 Pin Configuration

Table 13. ADuM3441 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2, 8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
3	V _{IA}	Logic Input A.
4	V _{IB}	Logic Input B.
5	V _{IC}	Logic Input C.
6	V _{OD}	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V_{OD} output is enabled when V_{E1} is high or disconnected. V_{OD} is disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V_{OA} , V_{OB} , and V_{OC} outputs are enabled when V_{E2} is high or disconnected. V_{OA} , V_{OB} , and V_{OC} outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.
11	V _{ID}	Logic Input D.
12	V _{oc}	Logic Output C.
13	V _{OB}	Logic Output B.
14	V_{OA}	Logic Output A.
16	V_{DD2}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.



*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO ${\rm GND_1}$ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO ${\rm GND_2}$ IS RECOMMENDED.

Figure 7. ADuM3442 Pin Configuration

Table 14. ADuM3442 Pin Function Descriptions

Pin No.	Mnemonic	Function
1	V_{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2,8	GND₁	Ground 1. Ground reference for Isolator Side 1.
3	VIA	Logic Input A.
4	V_{IB}	Logic Input B.
5	V _{oc}	Logic Output C.
6	V _{OD}	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V_{OC} and V_{OD} outputs are enabled when V_{E1} is high or disconnected. V_{OC} and V_{OD} outputs are disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V_{OA} and V_{OB} outputs are enabled when V_{E2} is high or disconnected. V_{OA} and V_{OB} outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.
11	V _{ID}	Logic Input D.
12	V _{IC}	Logic Input C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
16	V_{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.

TYPICAL PERFORMANCE CHARACTERISTICS

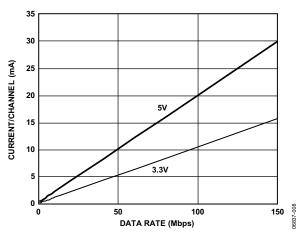


Figure 8. Typical Input Supply Current per Channel vs. Data Rate for 5 V and 3.3 V Operation

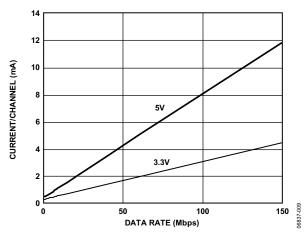


Figure 9. Typical Output Supply Current per Channel vs. Data Rate for 5 V and 3.3 V Operation (No Output Load)

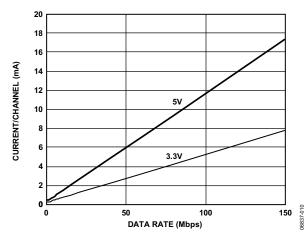


Figure 10. Typical Output Supply Current per Channel vs. Data Rate for 5 V and 3.3 V Operation (15 pF Output Load)

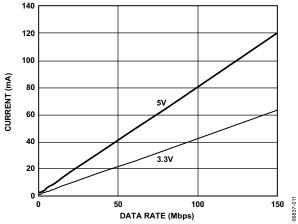


Figure 11. Typical ADuM3440 $V_{\rm DD1}$ Supply Current vs. Data Rate for 5 V and 3.3 V Operation

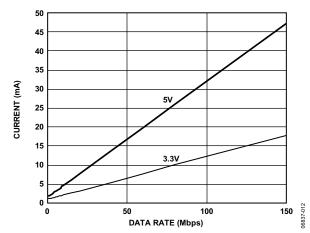


Figure 12. Typical ADuM3440 $V_{\rm DD2}$ Supply Current vs. Data Rate for 5 V and 3.3 V Operation

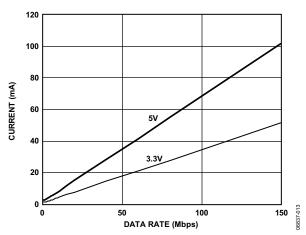


Figure 13. Typical ADuM3441 V_{DD1} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

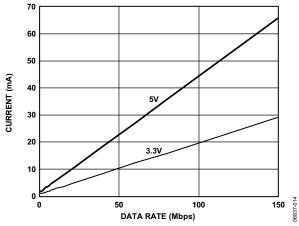


Figure 14. Typical ADuM3441 $V_{\rm DD2}$ Supply Current vs. Data Rate for 5 V and 3.3 V Operation

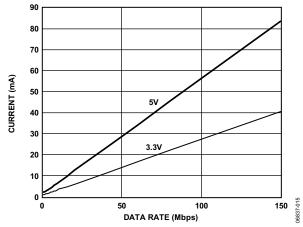


Figure 15. Typical ADuM3442 $V_{\rm DD1}$ or $V_{\rm DD2}$ Supply Current vs.Data Rate for 5 V and 3.3 V Operation

APPLICATIONS INFORMATION

PC BOARD LAYOUT

The ADuM344x digital isolator requires no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at the input and output supply pins (see Figure 16). Bypass capacitors are most conveniently connected between Pin 1 and Pin 2 for $V_{\rm DD1}$ and between Pin 15 and Pin 16 for $V_{\rm DD2}$. The capacitor value should be between 0.01 μF and 0.1 μF . The total lead length between both ends of the capacitor and the input power supply pin should not exceed 20 mm. Bypassing between Pin 1 and Pin 8 and between Pin 9 and Pin 16 should be considered unless the ground pair on each package side is connected close to the package.

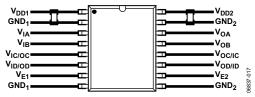


Figure 16. Recommended Printed Circuit Board Layout

In applications involving high common-mode transients, care should be taken to ensure that board coupling across the isolation barrier is minimized. Furthermore, the board layout should be designed such that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this could cause voltage differentials between pins exceeding the device's absolute maximum ratings, thereby leading to latch-up or permanent damage.

See the AN-1109 Application Note for board layout guidelines.

PROPAGATION DELAY-RELATED PARAMETERS

Propagation delay is a parameter that describes the time it takes a logic signal to propagate through a component. The propagation delay to a logic low output may differ from the propagation delay to a logic high.

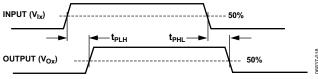


Figure 17. Propagation Delay Parameters

Pulse width distortion is the maximum difference between these two propagation delay values and is an indication of how accurately the input signal's timing is preserved.

Channel-to-channel matching refers to the maximum amount the propagation delay differs between channels within a single ADuM344x component.

Propagation delay skew refers to the maximum amount the propagation delay differs between multiple ADuM344x components operating under the same conditions.

SYSTEM-LEVEL ESD CONSIDERATIONS AND ENHANCEMENTS

System-level ESD reliability (for example, per IEC 61000-4-x) is highly dependent on system design, which varies widely by application. The ADuM344x incorporate many enhancements to make ESD reliability less dependent on system design. The enhancements include the following:

- ESD protection cells added to all input/output interfaces.
- Key metal trace resistances reduced using wider geometry and paralleling of lines with vias.
- The SCR effect inherent in CMOS devices is minimized by the use of guarding and isolation techniques between PMOS and NMOS devices.
- Areas of high electric field concentration eliminated using 45° corners on metal traces.
- Supply pin overvoltage prevented with larger ESD clamps between each supply pin and its respective ground.

While the ADuM344x improve system-level ESD reliability, they are no substitute for a robust system-level design. See the AN-793 application note, *ESD/Latch-Up Considerations with iCoupler Isolation Products* for detailed recommendations on board layout and system-level design.

DC CORRECTNESS AND MAGNETIC FIELD IMMUNITY

Positive and negative logic transitions at the isolator input cause narrow (~1 ns) pulses to be sent to the decoder via the transformer. The decoder is bistable and is, therefore, either set or reset by the pulses, indicating input logic transitions. In the absence of logic transitions at the input for more than ~1 μs , a periodic set of refresh pulses indicative of the correct input state are sent to ensure dc correctness at the output. If the decoder receives no internal pulses of more than about 5 μs , the input side is assumed unpowered or nonfunctional, in which case the isolator output is forced to a default state (see the Absolute Maximum Ratings section) by the watchdog timer circuit.

The limitation on the magnetic field immunity of the ADuM344x is set by the condition in which induced voltage in the receiving coil of the transformer is sufficiently large to either falsely set or reset the decoder. The following analysis defines the conditions under which this can occur. The 3 V operating condition of the ADuM344x is examined because it represents the most susceptible mode of operation.

The pulses at the transformer output have an amplitude greater than 1.0 V. The decoder has a sensing threshold at about 0.5 V, thus establishing a 0.5 V margin in which induced voltages can be tolerated.

The voltage induced across the receiving coil is given by

$$V = (-d\beta/dt)\sum_{n} \pi r_{n}^{2}; n = 1, 2, ..., N$$

where:

β is magnetic flux density (gauss).

N is the number of turns in the receiving coil.

 r_n is the radius of the nth turn in the receiving coil (cm).

Given the geometry of the receiving coil in the ADuM344x and an imposed requirement that the induced voltage be at most 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field is calculated as shown in Figure 18.

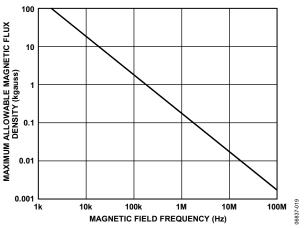


Figure 18. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.2 kgauss induces a voltage of 0.25 V at the receiving coil. This is about 50% of the sensing threshold and does not cause a faulty output transition. Similarly, if such an event were to occur during a transmitted pulse (and was of the worst-case polarity), it would reduce the received pulse from >1.0 V to 0.75 V—still well above the 0.5 V sensing threshold of the decoder.

The preceding magnetic flux density values correspond to specific current magnitudes at given distances from the ADuM344x transformers. Figure 19 expresses these allowable current magnitudes as a function of frequency for selected distances. As shown, the ADuM344x is extremely immune and can be affected only by extremely large currents operated at high frequency very close to the component. For the 1 MHz example noted, one would have to place a 0.5 kA current 5 mm away from the ADuM344x to affect the component's operation.

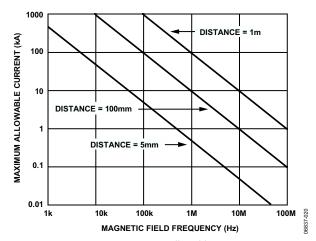


Figure 19. Maximum Allowable Current for Various Current-to-ADuM344x Spacings

Note that at combinations of strong magnetic field and high frequency, any loops formed by printed circuit board traces could induce error voltages sufficiently large enough to trigger the thresholds of succeeding circuitry. Care should be taken in the layout of such traces to avoid this possibility.

POWER CONSUMPTION

The supply current at a given channel of the ADuM344x isolator is a function of the supply voltage, the channel's data rate, and the channel's output load.

For each input channel, the supply current is given by

$$\begin{split} I_{DDI} &= I_{DDI\,(Q)} \\ I_{DDI} &= I_{DDI\,(D)} \times (2f - f_r) + I_{DDI\,(O)} \end{split} \qquad \qquad f \leq 0.5\,f_r \end{split}$$

For each output channel, the supply current is given by

$$\begin{split} I_{DDO} &= I_{DDO\,(Q)} \\ I_{DDO} &= (I_{DDO\,(D)} + (0.5 \times 10^{-3}) \times C_L \times V_{DDO}) \times (2f - f_r) + I_{DDO\,(Q)} \\ f &> 0.5 \, f_r \end{split}$$

where:

 $I_{DDI(D)}$, $I_{DDO(D)}$ are the input and output dynamic supply currents per channel (mA/Mbps).

 C_L is the output load capacitance (pF).

 V_{DDO} is the output supply voltage (V).

f is the input logic signal frequency (MHz); it is half of the input data rate expressed in units of Mbps.

 f_r is the input stage refresh rate (Mbps).

 $I_{\rm DDI\,(Q)},\,I_{\rm DDO\,(Q)}$ are the specified input and output quiescent supply currents (mA).

To calculate the total $V_{\rm DD1}$ and $V_{\rm DD2}$ supply current, the supply currents for each input and output channel corresponding to $V_{\rm DD1}$ and $V_{\rm DD2}$ are calculated and totaled. Figure 8 and Figure 9 provide per-channel supply currents as a function of data rate for an unloaded output condition. Figure 10 provides per-channel supply current as a function of data rate for a 15 pF output condition. Figure 11 through Figure 15 provide total $V_{\rm DD1}$ and $V_{\rm DD2}$ supply current as a function of data rate for ADuM3440/ADuM3441/ADuM3442 channel configurations.

INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the ADuM344x.

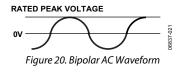
Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage. The values shown in Figure 20 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition, and the maximum CSA/VDE approved working voltages. In many cases, the approved working voltage is higher than the 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

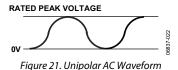
The insulation lifetime of the ADuM344x depends on the voltage waveform type imposed across the isolation barrier. The *i*Coupler insulation structure degrades at different rates depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 20, Figure 21, and Figure 22 illustrate these different isolation voltage waveforms.

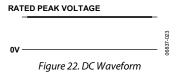
Bipolar ac voltage is the most stringent environment. The goal of a 50-year operating lifetime under the ac bipolar condition determines the maximum working voltage recommended by Analog Devices.

In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower, which allows operation at higher working voltages while still achieving a 50-year service life. The working voltages listed in Table 10 can be applied while maintaining the 50-year minimum lifetime provided the voltage conforms to either the unipolar ac or dc voltage cases. Any cross insulation voltage waveform that does not conform to Figure 21 or Figure 22 should be treated as a bipolar ac waveform and its peak voltage should be limited to the 50-year lifetime voltage value listed in Table 10.

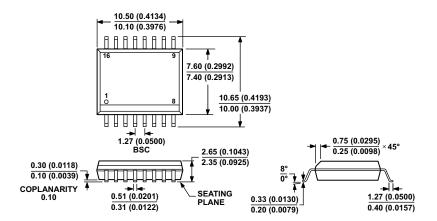
Note that the voltage presented in Figure 21 is shown as sinusoidal for illustration purposes only. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.







OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-013-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 23. 16-Lead Standard Small Outline Package [SOIC_W] Wide Body (RW-16) Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model 1, 2	Number of Inputs, V _{DD1} Side	Number of Inputs, V _{DD2} Side	Data Rate	Propagation	Maximum Pulse Width Distortion (ns)		Package Description	Package Option
ADuM3440CRWZ	4	0	150	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3441CRWZ	3	1	150	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3442CRWZ	2	2	150	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16

¹ Z = RoHS Compliant Part.

² Tape and reel are available. The addition of an -RL suffix designates a 13" (1,000 units) tape-and-reel option.

NOTES

ADuM3440/ADuM3441/ADuM3442

NOTES

A	Du	M34	440/	/AD	uM3	441	/AD	OuM3	442
	D U			110	ullic	,	// 1	uivio	

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